

PATENT ASSIGNMENT

Electronic Version v1.1

Stylesheet Version v1.1

SUBMISSION TYPE:

NEW ASSIGNMENT

NATURE OF CONVEYANCE:

ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
Spancion Inc.	01/31/2007

RECEIVING PARTY DATA

Name:	Spancion LLC
Street Address:	915 DeGuigne Drive, P.O. Box 3453
Internal Address:	Mail Stop 250
City:	Sunnyvale
State/Country:	CALIFORNIA
Postal Code:	94088-3453

PROPERTY NUMBERS Total: 35

Property Type	Number
Patent Number:	6211020
Patent Number:	5940735
Patent Number:	6285054
Patent Number:	6764904
Patent Number:	6225659
Patent Number:	6303437
Patent Number:	6147377
Patent Number:	6344393
Patent Number:	6147378
Patent Number:	6225161
Patent Number:	5907561
Patent Number:	6555867
Patent Number:	6808988
Patent Number:	5981341

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Patent Number:	6027998
Patent Number:	6002160
Patent Number:	6309949
Patent Number:	6107169
Patent Number:	6306758
Patent Number:	6100559
Patent Number:	6258669
Patent Number:	6242773
Patent Number:	6034395
Patent Number:	6579778
Patent Number:	6174819
Patent Number:	6163049
Patent Number:	6413820
Patent Number:	6063662
Patent Number:	5972751
Patent Number:	6252276
Patent Number:	6001713
Patent Number:	6251717
Patent Number:	6034394
Patent Number:	6274433
Patent Number:	6989319

CORRESPONDENCE DATA

Fax Number: (408)616-3762

Correspondence will be sent via US Mail when the fax attempt is unsuccessful.

Phone: 408-616-3722

Email: sally.nieto@spansion.com

Correspondent Name: Raymond E. Fritz

Address Line 1: 915 DeGuigne Drive, P.O. Box 3453

Address Line 2: Mail Stop 250

Address Line 4: Sunnyvale, CALIFORNIA 94088-3453

NAME OF SUBMITTER:	Raymond E. Fritz
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Total Attachments: 4

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ASSIGNMENT AGREEMENT

This Assignment Agreement by and between **SPANSION INC.**, a corporation of Delaware having a place of business at 915 DeGuigne Drive, P. O. Box 3453, Sunnyvale, California 94088-3453, U.S.A., its affiliates and subsidiaries, (hereinafter referred to as "ASSIGNOR") and **SPANSION LLC**, a limited liability company of Delaware, having a place of business at 915 DeGuigne Drive, P. O. Box 3453, Sunnyvale, California, 94088-3453, U.S.A. (hereinafter "ASSIGNEE") is effective on the 21st day of December, 2005.

In consideration of good and valuable consideration, the receipt of which is hereby acknowledged, ASSIGNOR hereby assigns, transfers and conveys all of their right, title and interest in the United States and throughout the world in and to all invention disclosures, United States patent applications, United States patents, foreign patents, and foreign patent applications (including any Patent Cooperation Treaty (PCT) applications) identified on Schedule A attached hereto and made a part hereof, and the entire right, title and interest in the United States and throughout the world in and to the inventions to which said invention disclosures, patents and patent applications pertain, in and to all worldwide rights of priority, and in and to any corresponding United States and foreign patents, extensions and renewals of patents, results of reexamination, substitutions, reissues, patent applications, divisionals, continuations, continuations-in-part, utility models, petty patents, patents of importation, invention registrations, and inventor's certificates, together with all the rights and privileges granted and secured by said patents, extensions and renewals of patents, results of reexamination, substitutions, reissues, patent applications, divisionals, continuations, continuations-in-part, utility models, petty patents, patents of importation, invention registrations and inventor's certificates, including without limitation all claims, demands, rights and causes of action that ASSIGNOR may have against others on account of any past, present and future infringement of any of said patents, patent applications, utility models, petty patents, patents of importation, invention registrations, and inventor's certificates with the right in ASSIGNEE to sue for and obtain all relief to which ASSIGNOR may have been entitled by reason of any such infringement. ASSIGNOR further agrees that ASSIGNEE may apply for and receive Letters Patent, utility models, petty patents, patents of importation, invention registrations, and inventor's certificates for said inventions in its own name.

Said entire right, title, and interest is to be held and enjoyed by ASSIGNEE for its own use and benefit and for the use and benefit of its successors and assigns, to the full end of the term for which said patents, registrations or certificates may be granted, as fully and entirely as the same would have been held and enjoyed by ASSIGNOR had this assignment and sale not been made.

ASSIGNOR's assignment, transference and conveyance of all of its right, title and interest in the United States and throughout the world hereunder is made subject to any rights, licenses or immunities relating to such rights, titles and interests that have been granted to any persons by ASSIGNOR or its assignors.

IN WITNESS WHEREOF, the ASSIGNOR and ASSIGNEE have caused this Assignment Agreement to be executed by their respective duly authorized representatives as of December 21, 2005.

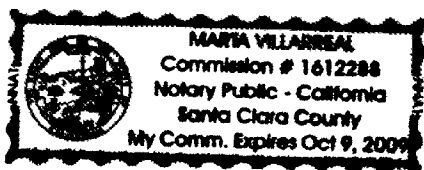
**ASSIGNOR
SPANSION INC.**

By: [Signature]
Name: Robert C. Melendres
Title: Executive Vice President, Corporate Development,
General Counsel and Corporate Secretary

Date: January 31, 2007

State of **CALIFORNIA**)
County of **SANTA CLARA**)

On January 31, 2007, before me, Marta Villarreal, a Notary Public, personally appeared Robert C. Melendres, personally known to me or proved to me on the basis of satisfactory evidence to be the person whose name is subscribed to the within instrument and acknowledged to me that he/she executed the same in his/her authorized capacity, and that by his/her signature on the instrument the person, or the entity upon behalf of which the person acted, executed the instrument.



Witness my hand and official seal.

[Signature]
SIGNATURE OF NOTARY

**ASSIGNEE
SPANSION LLC**

By: [Signature]
Name: Robert C. Melendres
Title: Executive Vice President, Corporate Development,
General Counsel and Corporate Secretary

Date: January 31, 2007

State of CALIFORNIA)
County of SANTA CLARA)

On January 31, 2001, before me, Marta Villarreal, a Notary Public, personally appeared Rodriguez C. Melendez, personally known to me or proved to me on the basis of satisfactory evidence to be the person whose name is subscribed to the within instrument and acknowledged to me that he/she executed the same in his/her authorized capacity, and that by his/her signature on the instrument the person, or the entity upon behalf of which the person acted, executed the instrument.

Witness my hand and official seal.



Marta Villarreal
SIGNATURE OF NOTARY

Docket No.	Country	Status	Application	File Date	Grant Date	Owner	Patent No.	Title
C521397	USA	Granted	09/177,294	10/22/1998	4/3/2001	A2S	6,211,020	PROCESS FOR FABRICATING A COMMON SOURCE
C526397	USA	Granted	08/917,149	8/25/1997	8/17/1999	A2S	5,940,735	REDUCTION OF CHARGE LOSS IN NONVOLATILE
C553397	USA	Granted	09/052,057	3/30/1998	9/4/2001	A2S	6,285,054	TRENCHED GATE NON-VOLATILE SEMICONDUCTOR
C553397	USA	Granted	09/629,780	7/31/2000	7/20/2004	A2S	6,764,904	TRENCHED GATE NON-VOLATILE SEMICONDUCTOR
C554397	USA	Granted	09/052,058	3/30/1998	5/1/2001	A2S	6,225,659	TRENCHED GATE SEMICONDUCTOR DEVICE AND
C554397	USA	Granted	09/632,536	8/4/2000	10/16/2001	A2S	6,303,437	TRENCHED GATE NON-VOLATILE SEMICONDUCTOR
C555397	USA	Granted	09/052,061	3/30/1998	11/14/2000	A2S	6,147,377	FULLY RECESSED SEMICONDUCTOR DEVICE
C555397	USA	Granted	09/620,339	7/20/2000	2/5/2002	A2S	6,344,393	FULLY RECESSED SEMICONDUCTOR DEVICE AND
C557397	USA	Granted	09/052,060	3/30/1998	11/14/2000	A2S	6,147,378	FULLY RECESSED SEMICONDUCTOR DEVICE AND
C557397	USA	Granted	09/470,568	12/22/1999	5/1/2001	A2S	6,225,161	FULLY RECESSED SEMICONDUCTOR DEVICE AND
C560497	USA	Granted	08/992,077	12/17/1997	5/25/1999	A2S	5,907,561	METHOD TO IMPROVE TESTING SPEED OF MEMORY
C610497	USA	Granted	08/991,448	2/8/2000	4/29/2003	A2S	6,555,867	FLASH MEMORY GATE COUPLING USING HSG
C611497	USA	Granted	09/019,409	2/5/1998	10/26/2004	A2S	6,808,988	METHOD FOR FORMING ISOLATION IN FLASH
C612497	USA	Granted	08/986,160	12/5/1997	11/9/1999	A2S	5,981,341	SIDEWALL SPACER FOR PROTECTING TUNNEL
C617497	USA	Granted	08/992,536	12/17/1997	2/22/2000	A2S	6,027,998	METHOD FOR FULLY PLANARIZED CONDUCTIVE LINE
C623497	USA	Granted	08/989,820	12/12/1997	12/14/1999	A2S	6,002,160	A SEMICONDUCTOR ISOLATION PROCESS TO
C623497	USA	Granted	09/440,934	11/16/1999	10/30/2001	A2S	6,309,949	SEMICONDUCTOR ISOLATION PROCESS TO
C625497	USA	Granted	09/134,526	8/14/1998	8/22/2000	A2S	6,107,169	METHOD FOR FABRICATING A DOPED POLYSILICON
C628497	USA	Granted	09/567,534	5/10/2000	10/23/2001	A2S	6,306,758	MULTIPURPOSE GRADED SILICON OXYNITRIDE CAP
C628497	USA	Granted	09/134,525	1/6/2000	8/8/2000	A2S	6,100,559	MULTIPURPOSE GRADED SILICON OXYNITRIDE CAP
C627497	USA	Granted	08/992,960	12/17/1999	7/10/2001	A2S	6,258,669	METHODS AND ARRANGEMENTS FOR IMPROVED
C628497	USA	Granted	09/163,310	9/7/2000	6/5/2001	A2S	6,242,773	SELF-ALIGNING POLY 1 ONO DIELECTRIC
C629497	USA	Granted	09/092,352	6/5/1998	3/7/2000	A2S	6,034,395	METHODS AND ARRANGEMENTS FOR REDUCING
C630497	USA	Granted	09/634,991	8/8/2000	6/17/2003	A2S	6,579,778	SOURCE BUS FORMATION FOR A FLASH MEMORY
C634497	USA	Granted	09/119,777	7/21/1998	1/16/2001	A2S	6,174,819	LOW TEMPERATURE PHOTORESIST REMOVAL FOR
C636497	USA	Granted	09/170,061	10/13/1998	12/19/2000	A2S	6,163,049	METHOD OF FORMING A COMPOSITE INTERPOLY
C636497	USA	Granted	09/725,843	11/30/2000	7/2/2002	A2S	6,413,820	METHOD OF FORMING A COMPOSITE INTERPOLY
C638497	USA	Granted	08/993,409	11/10/1999	5/16/2000	A2S	6,063,662	METHODS FOR FORMING A CONTROL GATE
C640497	USA	Granted	09/143,090	8/28/1998	10/26/1999	A2S	5,972,751	METHODS AND ARRANGEMENTS FOR INTRODUCING
C640497	USA	Granted	09/377,183	8/19/1999	6/26/2001	A2S	6,252,276	NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE
C641497	USA	Granted	09/154,074	9/16/1998	12/14/1999	A2S	6,001,713	METHODS FOR FORMING NITROGEN-RICH REGIONS
C643497	USA	Granted	09/163,315	10/10/2000	6/26/2001	A2S	6,251,717	VIABLE MEMORY CELL FORMED USING RAPID
C644497	USA	Granted	08/992,950	12/16/1997	3/7/2000	A2S	6,034,394	METHODS AND ARRANGEMENTS FOR FORMING A
C644497	USA	Granted	09/476,121	1/3/2000	8/14/2001	A2S	6,274,433	METHODS AND ARRANGEMENTS FOR FORMING A
C645497	USA	Granted	10/718,707	11/24/2003	1/24/2006	A2S	6,989,319	METHODS FOR FORMING NITROGEN-RICH REGIONS